

## General Purpose NPN Epitaxial Planar Transistor

# BTC3906M3

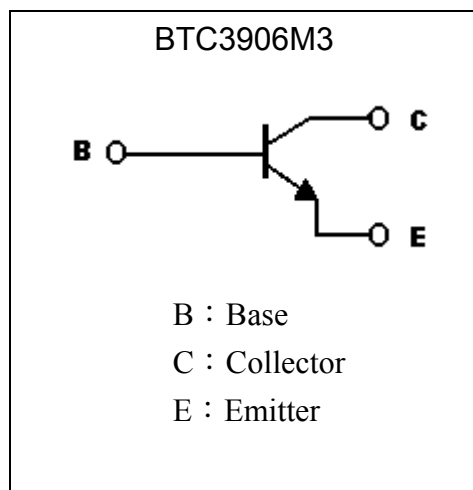
### Description

The BTC3906M3 is designed for general purpose applications requiring high breakdown voltage.

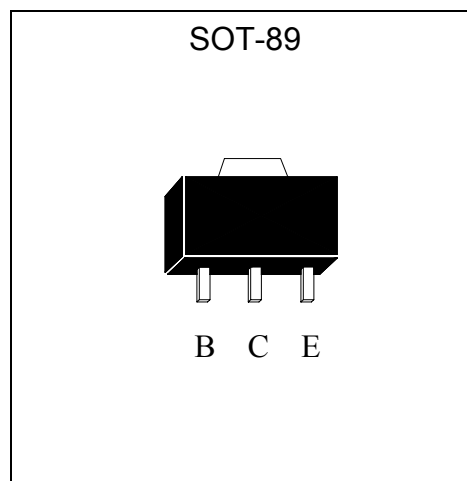
### Features

- High collector-emitter breakdown voltage. ( $BV_{CEO}=160V$  @  $I_C=1mA$ )
- Complement to BTA1514M3

### Symbol



### Outline



### Absolute Maximum Ratings ( $T_a=25^{\circ}C$ )

Parameter	Symbol	Limits	Unit
Collector-Base Voltage	$V_{CBO}$	180	V
Collector-Emitter Voltage	$V_{CEO}$	160	V
Emitter-Base Voltage	$V_{EBO}$	6	V
Collector Current	$I_C$	600	mA
Power Dissipation	$P_d$	0.6	W
		1 (Note 1)	W
		2 (Note 2)	W
Junction Temperature	$T_j$	150	$^{\circ}C$
Storage Temperature	$T_{stg}$	-55~+150	$^{\circ}C$

Note : 1. When mounted on FR-4 PCB with area measuring  $10 \times 10 \times 1$  mm

2. When mounted on ceramic with area measuring  $40 \times 40 \times 1$  mm

**Characteristics (Ta=25°C)**

Symbol	Min.	Typ.	Max.	Unit	Test Conditions
BV <sub>CBO</sub>	180	-	-	V	I <sub>C</sub> =100μA
BV <sub>CEO</sub>	160	-	-	V	I <sub>C</sub> =1mA
BV <sub>EBO</sub>	6	-	-	V	I <sub>E</sub> =10μA
I <sub>CBO</sub>	-	-	50	nA	V <sub>CB</sub> =120V
I <sub>EBO</sub>	-	-	50	nA	V <sub>EB</sub> =4V
*V <sub>CE(sat)</sub> 1	-	0.1	0.15	V	I <sub>C</sub> =10mA, I <sub>B</sub> =1mA
*V <sub>CE(sat)</sub> 2	-	-	0.2	V	I <sub>C</sub> =50mA, I <sub>B</sub> =5mA
*V <sub>BE(sat)</sub> 1	-	-	1	V	I <sub>C</sub> =10mA, I <sub>B</sub> =1mA
*V <sub>BE(sat)</sub> 2	-	-	1	V	I <sub>C</sub> =50mA, I <sub>B</sub> =5mA
*h <sub>FE</sub> 1	25	-	-	-	V <sub>CE</sub> =5V, I <sub>C</sub> =1mA
*h <sub>FE</sub> 2	60	-	-	-	V <sub>CE</sub> =5V, I <sub>C</sub> =10mA
*h <sub>FE</sub> 3	40	-	-	-	V <sub>CE</sub> =5V, I <sub>C</sub> =50mA
*h <sub>FE</sub> 4	52	-	390	-	V <sub>CE</sub> =6V, I <sub>C</sub> =2mA
f <sub>T</sub>	100	-	-	MHz	V <sub>CE</sub> =20V, I <sub>C</sub> =10mA, f=100MHz
Cob	-	-	6	pF	V <sub>CB</sub> =20V, I <sub>E</sub> =0A, f=1MHz

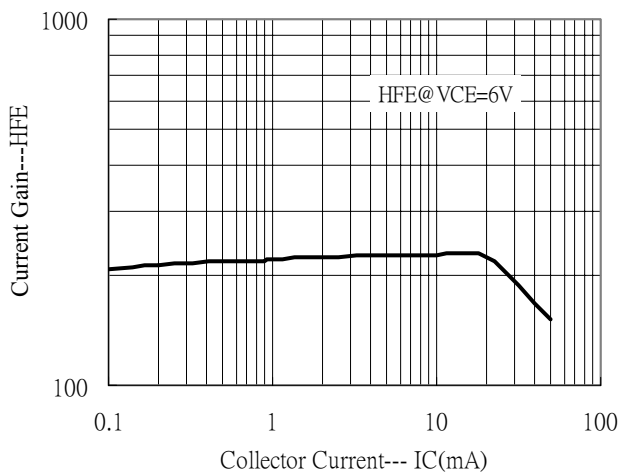
\*Pulse Test: Pulse Width ≤380μs, Duty Cycle≤2%

**Classification Of h<sub>FE</sub> 4**

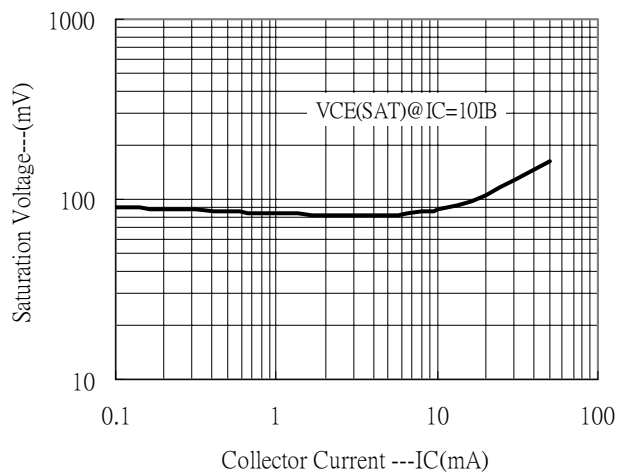
Rank	K	P	Q	R
Range	52~120	82~180	120~270	180~390

## Characteristic Curves

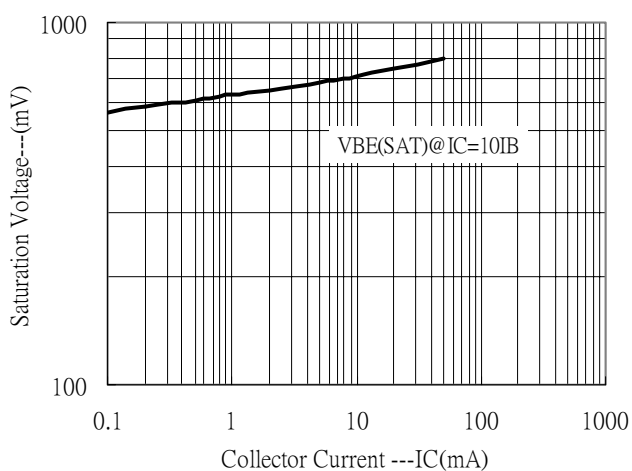
Current Gain vs Collector Current



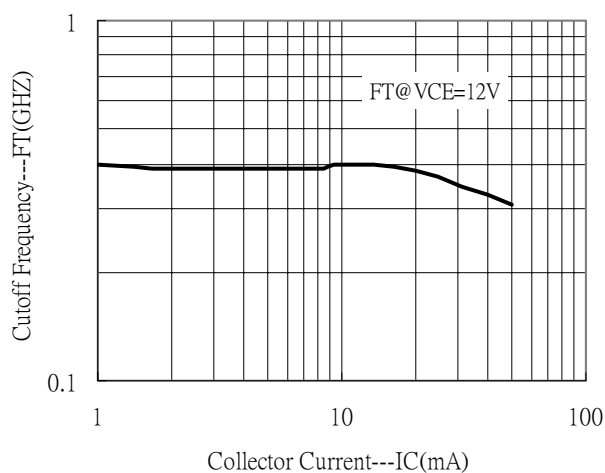
Saturation Voltage vs Collector Current



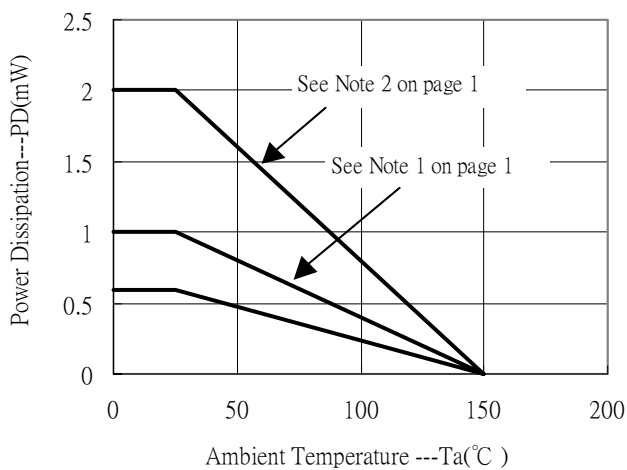
Saturation Voltage vs Collector Current



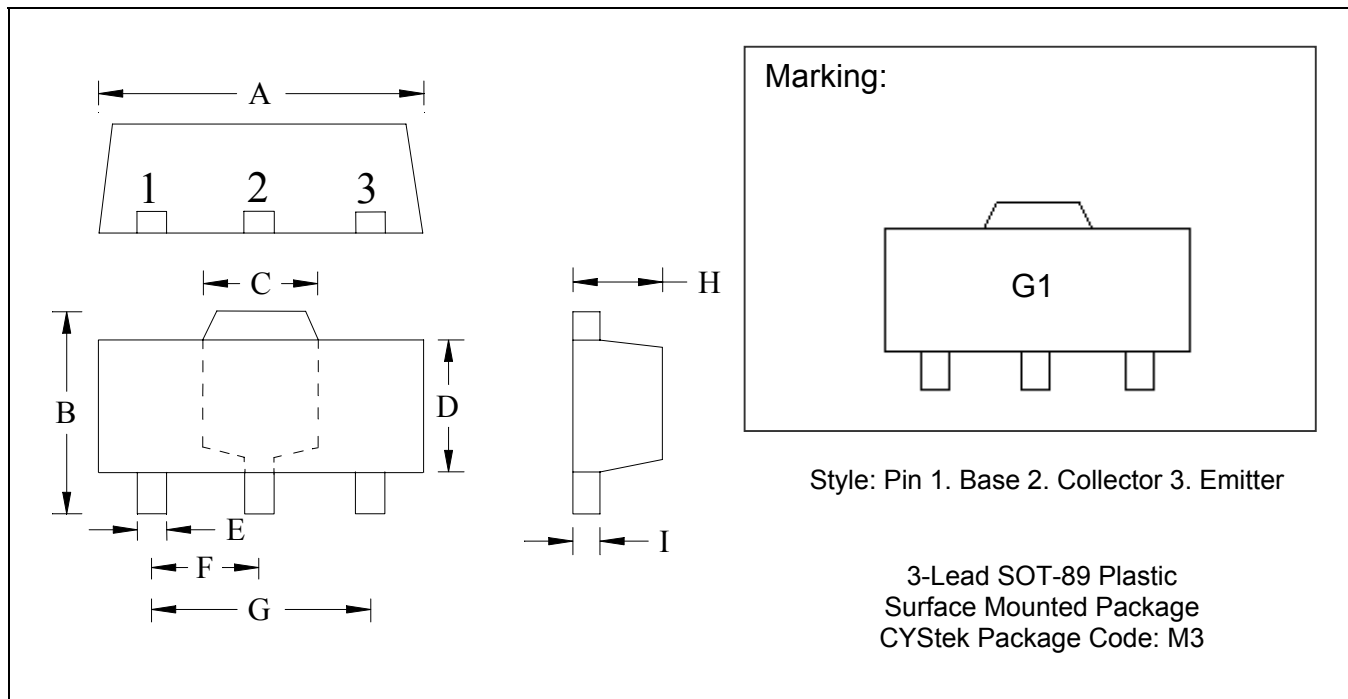
Cutoff Frequency vs Collector Current



Power Derating Curves



## SOT-89 Dimension



\*: Typical

DIM	Inches		Millimeters		DIM	Inches		Millimeters	
	Min.	Max.	Min.	Max.		Min.	Max.	Min.	Max.
A	0.1732	0.1811	4.40	4.60	F	0.0583	0.0598	1.48	1.527
B	0.1594	0.1673	4.05	4.25	G	0.1165	0.1197	2.96	3.04
C	0.0591	0.0663	1.50	1.70	H	0.0551	0.0630	1.40	1.60
D	0.0945	0.1024	2.40	2.60	I	0.0138	0.0161	0.35	0.41
E	0.01417	0.0201	0.36	0.51					

**Notes:** 1.Controlling dimension: millimeters.

2.Maximum lead thickness includes lead finish thickness, and minimum lead thickness is the minimum thickness of base material.

3.If there is any question with packing specification or packing method, please contact your local CYStek sales office.

### Material:

- Lead: 42 Alloy ; solder plating
- Mold Compound: Epoxy resin family, flammability solid burning class: UL94V-0

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